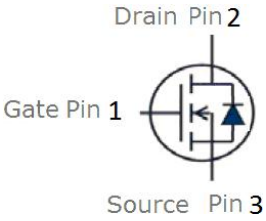
Features

- N-Channel，5V Logic Level Control
- Enhancement mode
- Very low on-resistance $R_{DS(on)}$ @ V_{GS}=4.5 V
- VitoMOS® Ⅱ Technology
- 100% Avalanche test
- Pb-free lead plating; RoHS compliant

Pb-Free RoHS HF Halogen-Free

V_{DS}	100	V
$R_{DS(on),TYP}$@ V_{GS}=10 V	6	mΩ
$R_{DS(on),TYP}$@ V_{GS}=4.5 V	7.8	mΩ
I_D	94	A

TO-251SSL



Part ID	Package Type	Marking	Tape and reel information
VSI008N10MS5	TO-251SSL	008N10M	75pcs/Tube

Maximum ratings, at T_A=25°C, unless otherwise specified

Symbol	Parameter		Rating	Unit
$V_{(BR)DSS}$	Drain-Source breakdown voltage		100	V
VGS	Gate-Source voltage		±20	V
I_S	Diode continuous forward current	T_C=25°C	94	A
I_D	Continuous drain current @VGS=10V	T_C=25°C	94	A
		T_C=100°C	67	A
I_{DM}	Pulse drain current tested ①	T_C=25°C	376	A
I_{DSM}	Continuous drain current @VGS=10V	T_A=25°C	10	A
		T_A=70°C	8	A
EAS	Avalanche energy, single pulsed ②		41	mJ
P_D	Maximum power dissipation	T_C=25°C	107	W
P_{DSM}	Maximum power dissipation ③	T_A=25°C	1.25	W
T_{STG}, T_J	Storage and Junction Temperature Range		-55 to 175	°C

Thermal Characteristics

Symbol	Parameter	Typical	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	1.4	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	100	°C/W

Electrical Characteristics

Symbol	Parameter	Condition	Min.	Typ.	Max.	Unit
Static Electrical Characteristics @ T_j=25°C (unless otherwis e stated)						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250μA	100	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=100V,V_{GS}=0V	--	--	1	μA
	Zero Gate Voltage Drain Current(T_j=125℃)	V_{DS}=100V,V_{GS}=0V	--	--	100	μA
I_{GSS}	Gate-Body Leakage Current	V_{GS}=±20V,V_{DS}=0V	--	--	±100	nA
$V_{GS(TH)}$	Gate Threshold Voltage	V_{DS}=V_{GS},I_D=250μA	1.5	--	2.5	V
$R_{DS(ON)}$	Drain-Source On-State Resistance ④	V_{GS}=10V, I_D=20A	--	6	8.5	mΩ
$R_{DS(ON)}$	Drain-Source On-State Resistance ④	V_{GS}=4.5V, I_D=15A	--	7.8	11	mΩ
Dynamic Electrical Characteristics @ T_j = 25°C (unless otherwise stated)						
C_{iss}	Input Capacitance	V_{DS}=30V,V_{GS}=0V, f=1MHz	2250	2645	3050	pF
C_{oss}	Output Capacitance		980	1155	1305	pF
C_{rss}	Reverse Transfer Capacitance		25	35	45	pF
R_g	Gate Resistance	f=1MHz	--	3.2	--	Ω
Q_g (10V)	Total Gate Charge	V_{DS}=50V,I_D=20A, V_{GS}=10V	--	45	--	nC
Q_g (4.5V)	Total Gate Charge		--	23	--	nC
Q_{gs}	Gate-Source Charge		--	8	--	nC
Q_{gd}	Gate-Drain Charge		--	9	--	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	V_{DD}=50V, I_D=20A, R_G=3Ω, V_{GS}=10V	--	11.7	--	ns
t_r	Turn-on Rise Time		--	7.2	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	34.5	--	ns
t_f	Turn-Off Fall Time		--	12.3	--	ns
Source- Drain Diode Characteristics@ T_j = 25°C (unless otherwise stated)						
V_{SD}	Forward on voltage	I_{SD}=20A,V_{GS}=0V	--	0.8	1.2	V
t_{rr}	Reverse Recovery Time	T_j=25℃,I_{sd}=20A, V_{GS}=0V di/dt=500A/μs	--	21.6	--	ns
Q_{rr}	Reverse Recovery Charge		--	44.7	--	nC

NOTE:

① Repetitive rating; pulse width limited by max junction temperature.

② Limited by T_{Jmax}, starting T_J = 25°C, L = 0.5mH,R_G = 25Ω, I_{AS} = 10A, V_{GS} =10V. Part not recommended for use above this value

③ The power dissipation P_{DSM} is based on $R_{\theta JA}$ and the maximum allowed junction temperature of 150°C.

④ Pulse width ≤ 300μs; duty cycle≤ 2%.

Typical Characteristics

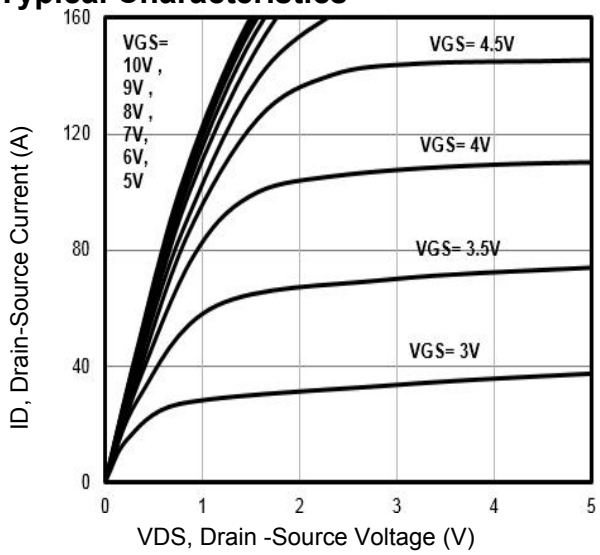


Fig1. Typical Output Characteristics

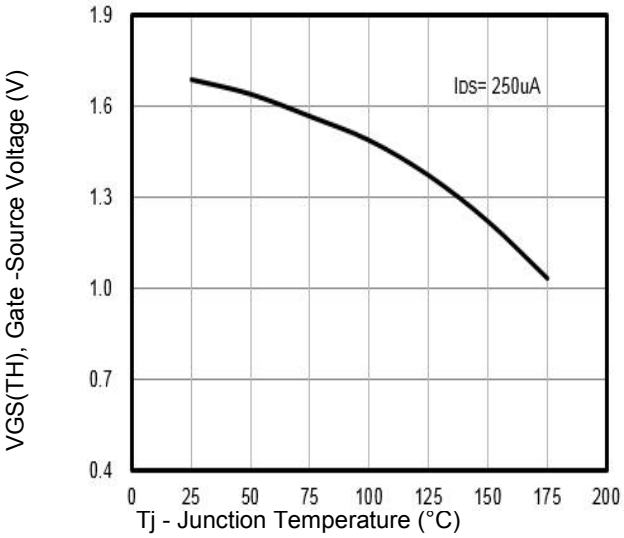


Fig2. $V_{GS(TH)}$ Gate -Source Voltage Vs. Tj

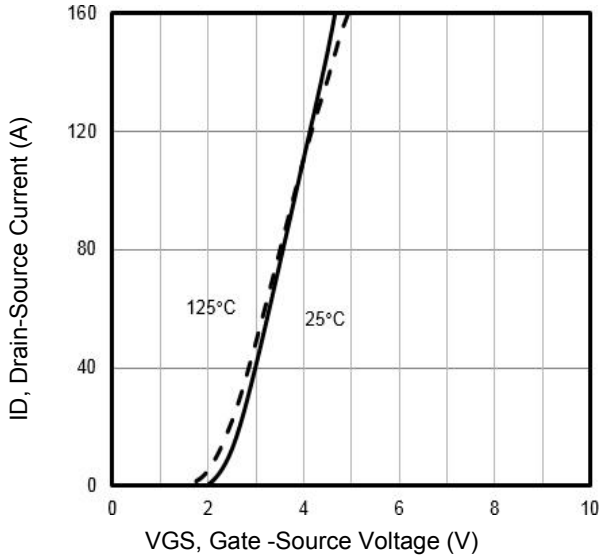


Fig3. Typical Transfer Characteristics

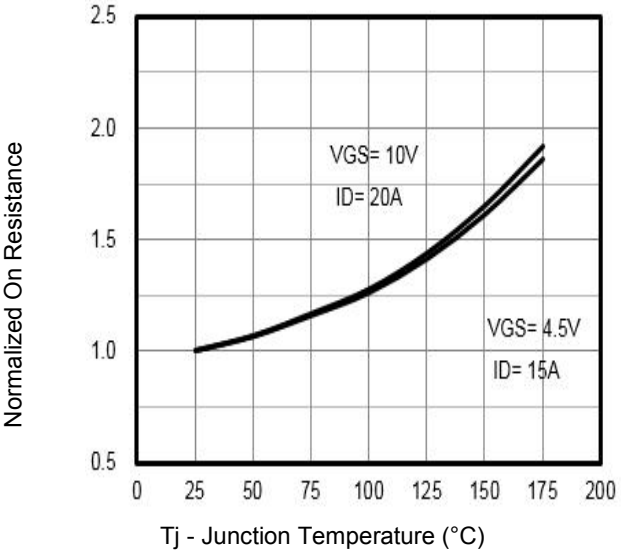


Fig4. Normalized On-Resistance Vs. Tj

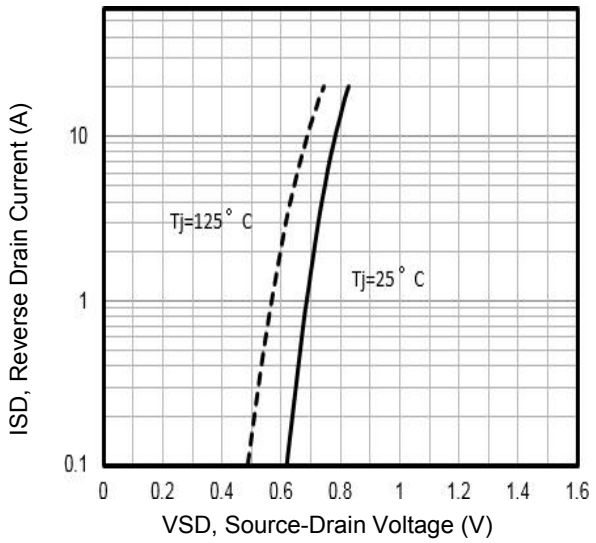


Fig5. Typical Source-Drain Diode Forward Voltage

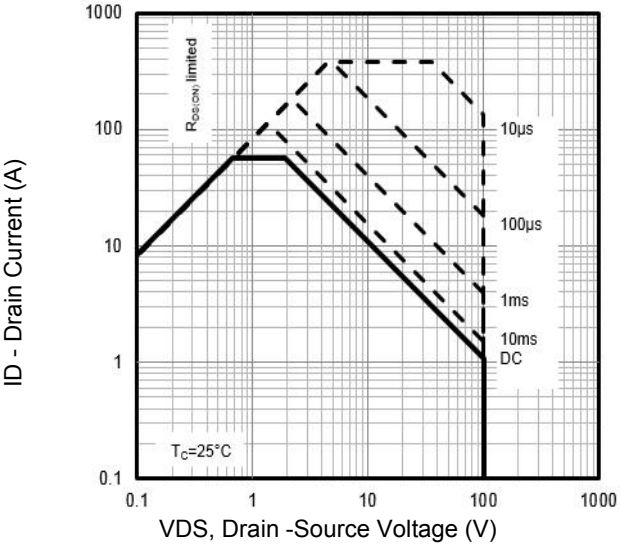


Fig6. Maximum Safe Operating Area

Typical Characteristics

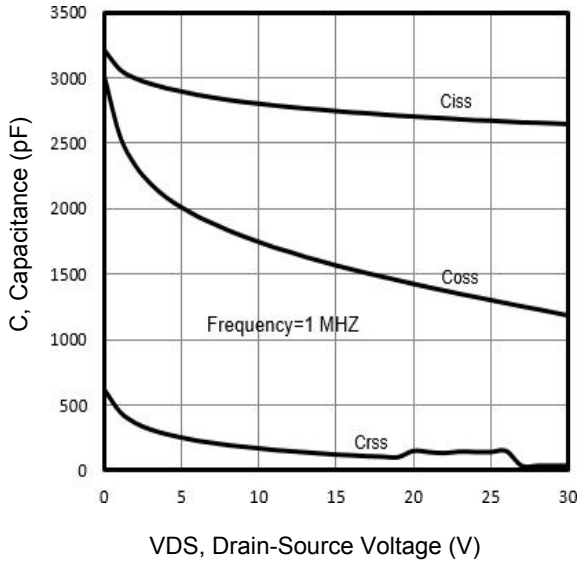


Fig7. Typical Capacitance Vs. Drain-Source Voltage

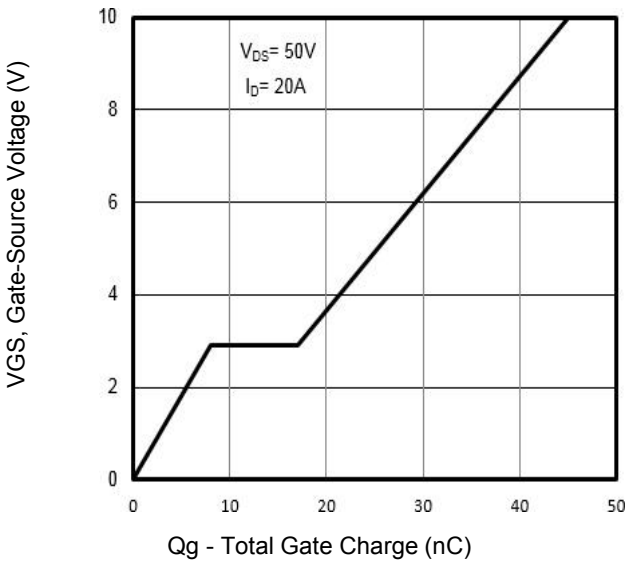


Fig8. Typical Gate Charge Vs. Gate-Source Voltage

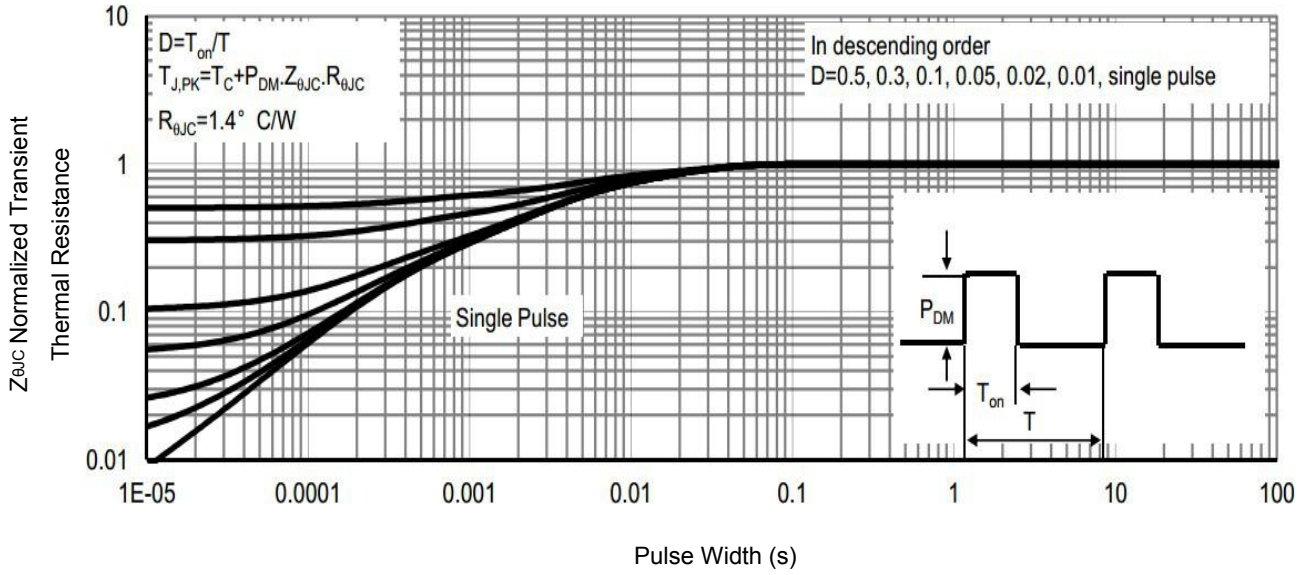


Fig9. Normalized Maximum Transient Thermal Impedance

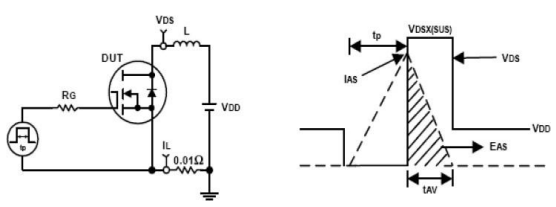


Fig10. Unclamped Inductive Test Circuit and waveforms

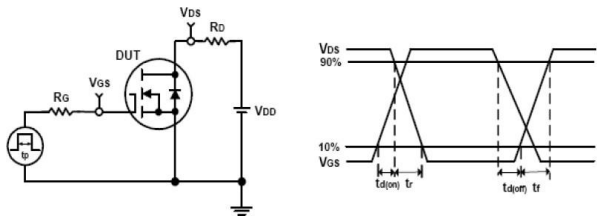
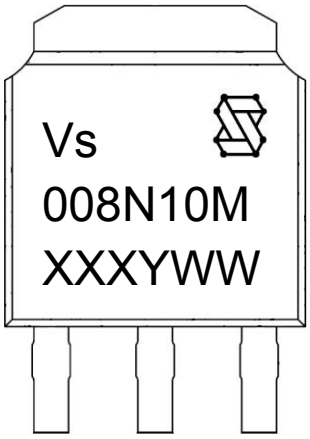


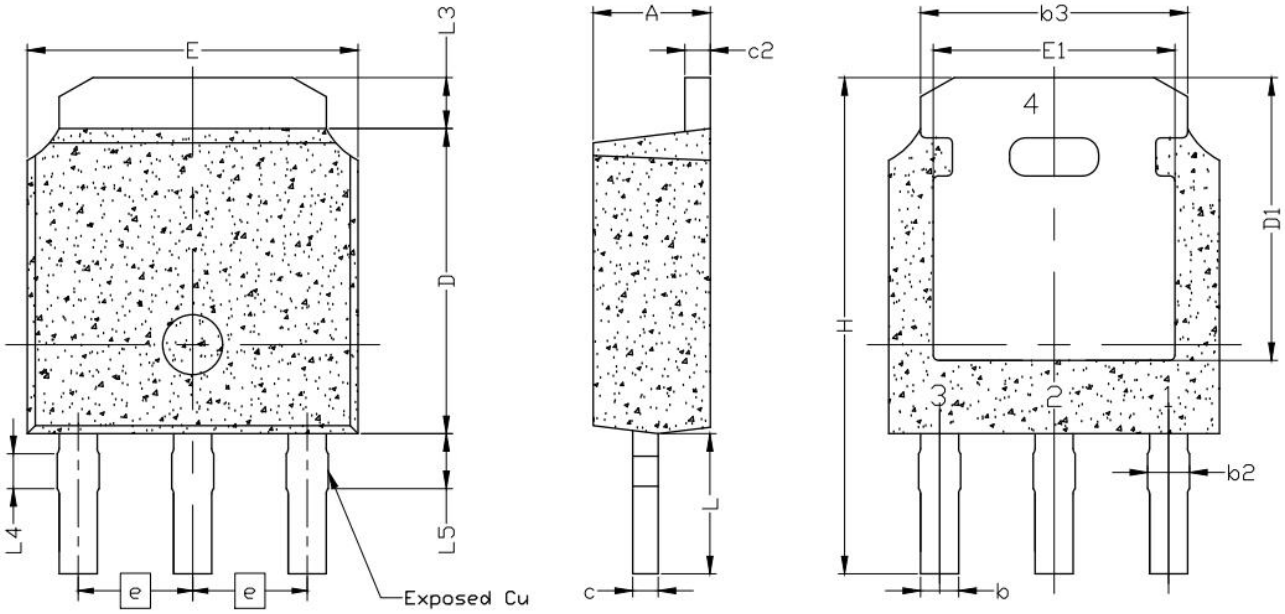
Fig11. Switching Time Test Circuit and waveforms

Marking Information



1st line： Vanguard Code（Vs）， Vanguard Logo
2nd line： Part Number（008N10M）
3rd line： Date code （XXXYWW）
XXX： Wafer Lot Number Code，code changed with Lot Number
Y： Year Code (e.g. E=2017, F=2018, G=2019, H=2020, etc)
WW： Week Code (01 to 53)

TO-251SSL Package Outline Data



Symbol	Dimensions (unit: mm)		
	Min	Typ	Max
A	2.2	2.3	2.38
b	0.64	0.76	0.88
b2	0.77	0.84	1.0
b3	5.21	5.34	5.46
c	0.4	0.5	0.6
c2	0.4	0.5	0.6
D	6.0	6.1	6.23
D1	5.1	--	--
E	6.4	6.6	6.73
E1	4.4	--	--
e	2.286 BSC		
H	9.65	9.90	10.05
L	2.65	2.80	2.95
L3	0.89	--	1.27
L4	0.698 REF		
L5	0.97	1.1	1.23

Note:

1. Dimension "D" and "E" do NOT include mold flash, protrusion or gate burrs. Mold flash, protrusion or gate burrs shall not exceed 0.1mm per side.

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